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B  
2202

PATENT

81784.0182

EXPRESS MAIL NO. EL713632637US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: YONEDA et al.

Art Unit: 2674

Serial No: 09/148,606

Examiner: A. Zamani

Filed: September 4, 1998

For: Semiconductor Device Having Laser  
Annealed Semiconductor Device, Display  
Device and Liquid Crystal Display Device

PRELIMINARY AMENDMENT

BOX CPA

U.S. PATENT AND TRADEMARK OFFICE

P.O. BOX 2327

ARLINGTON, VA 22202

Dear Sir:

Prior to the first Office Action of the above-referenced application, please amend the above-referenced application as follows:

IN THE CLAIMS:

Please replace the text of claims 1, 3, 5, 9-10, 14, 17-18, and 20-22 with the following text:

Sub  
C1  
B1  
1. (Amended) A semiconductor device in which a plurality of semiconductor elements are formed on a substrate, wherein in some or all of said semiconductor elements, a channel width of a channel region formed in a semiconductor layer to which laser annealing is applied is larger than a channel length thereof, and a channel width direction is neither vertical to nor parallel with regard to a side direction of said substrate.

B2  
cont  
Sub  
C2  
3. (Amended) A semiconductor device in which a plurality of semiconductor elements are formed on a substrate, wherein